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# P-Channel 40 V (D-S) MOSFEET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
- 40	$0.106 \text{ at V}_{GS} = -10 \text{ V}$	- 15 <sup>d</sup>		
- 40	0.125 at V <sub>GS</sub> = - 4.5 V	- 10 <sup>d</sup>		

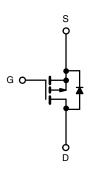
### **FEATURES**

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested



### **APPLICATIONS**

Load Switch



P-Channel MOSFET

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	$\bigcirc$	
T		$\overline{\mathbb{T}}$
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ABSOLUTE MAXIMUM RATINGS (T	$_{A}$ = 25 $^{\circ}$ C, unless othe	rwise noted)			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>.I</sub> = 175 °C)	T <sub>C</sub> = 25 °C	L	- 15 <sup>d</sup>	A	
Continuous Diam Current (1) = 173 C)	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 10.5		
Pulsed Drain Current		I <sub>DM</sub>	- 60		
Avalanche Current		I <sub>AS</sub>	- 15		
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	51	mJ	
Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	19 <sup>c</sup>	w	
	T <sub>A</sub> = 25 °C	' D	1.5 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	<u> </u>	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>b</sup>	t ≤ 10 s	- R <sub>thJA</sub>	40	50	°C/W
Junction-to-Ambient	Steady State		50	60	
Junction-to-Case		$R_{thJC}$	0.82	1.1	

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



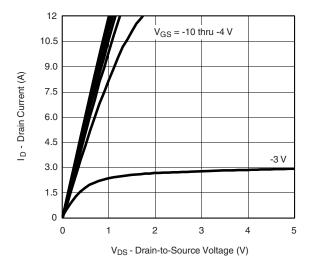
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 40			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = - 32 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			- 50	-50 μA	
		$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$			- 100		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 15			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A		0.106	0.130		
D . O . O D	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A, T <sub>J</sub> = 125 °C			0.145	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A, T <sub>J</sub> = 150 °C			0.157		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.125	0.150		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5 A		61		S	
Dynamic <sup>b</sup>	•						
Input Capacitance	C <sub>iss</sub>			1880			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		480		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			205			
Total Gate Charge <sup>c</sup>	$Q_g$			110	165		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5 \text{ A}$		23		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			18			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			15	23		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 0.6 $\Omega$		70	105		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_{D} = -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_{G} = 6\Omega$		155	235	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	]		175	260		
Source-Drain Diode Ratings and Cha	racteristics	T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>				- 15	^	
Pulsed Current	I <sub>SM</sub>				- 60	A	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = - 10 A, V <sub>GS</sub> = 0 V		- 0.7	- 1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 10 A, dl/dt = 100 A/μs		45	70	ns	

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

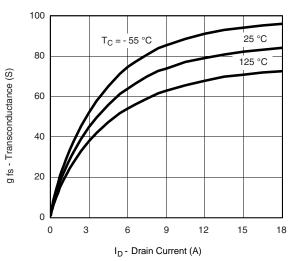
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



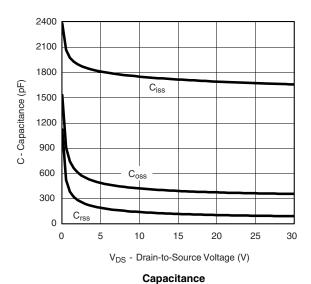
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



#### **Output Characteristics**

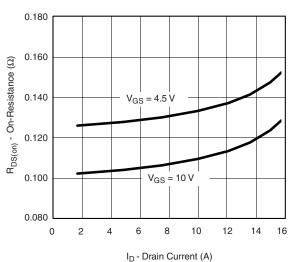


#### Transconductance

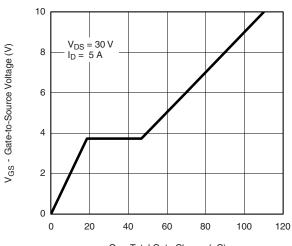


10.5 9.0 I<sub>D</sub> - Drain Current (A) 7.5 6.0 4.5 T<sub>C</sub> = 125 °C 3.0 25 °C 1.5 0.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 V<sub>GS</sub> - Gate-to-Source Voltage (V)

### Transfer Characteristics



#### On-Resistance vs. Drain Current

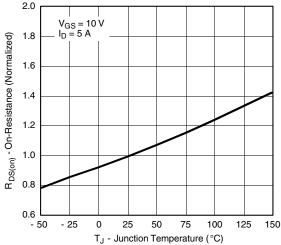


 $\mathbf{Q}_{\mathbf{g}}$  - Total Gate Charge (nC)

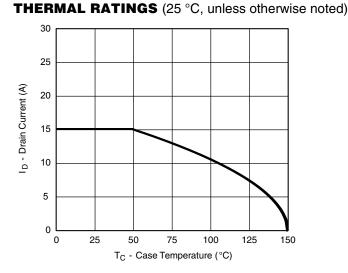
**Gate Charge** 



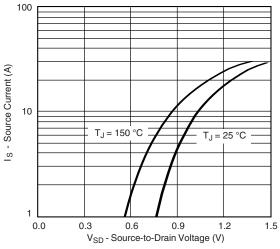
### **TYPICAL CHARACTERISTICS**



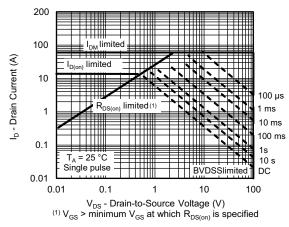
# On-Resistance vs. Junction Temperature



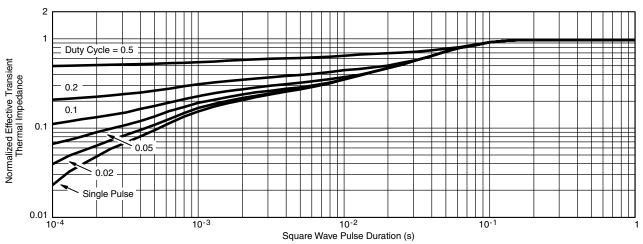
**Drain Current vs. Case Temperature** 



Source-Drain Diode Forward Voltage



Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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